CMF65R380

600V, 0.34Ω typ., 11A N-Channel Super Junction Power MOSFET

General Description

CMF65R380 is power MOSFET using Cmos's advanced super junction technology that can realize very low on resistance and gate charge. It will provide much high efficiency by using optimized charge coupling technology.
These user friendly devices give an advantage of low EMI to designers as well as low switching loss.

Product Summary

BVDSS	$R_{DS(on)}$ max.	ID
650V	0.38Ω	11A

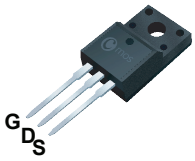
Applications

- Adaptor
- PFC power supply stages
- Switching applications

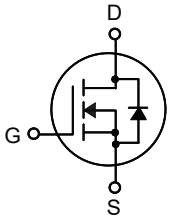
Features

- Multi-layer Epitaxial Chip Technology
- Low On-Resistance
- 100% avalanche tested
- RoHS Complian

TO-220F Pin Configuration



TO-220F
(CMF65R380)



Absolute Maximum Ratings (Tc=25℃ unless otherwise noted)

Symbol	Parameter	Rating	Units
V_{DSS}	Drain-Source Voltage	650	V
I_D	Drain Current - Continuous (T_C = 25℃)	11	A
	- Continuous (T_C = 100℃)	6.7	A
I_{DM}	Drain Current - Pulsed	44	A
V_{GSS}	Gate-Source Voltage	±30	V
E_{AS}	Single Pulsed Avalanche Energy [1]	75	mJ
P_D	Power Dissipation (T_C = 25℃)	31	W
T_J, T_{STG}	Operating and Storage Temperature Range	-55 to +150	℃

Thermal Characteristics

Symbol	Parameter	Rating	Units
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case	4.1	℃/W
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient	75	℃/W

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Electrical Characteristic (T_C=25℃ unless otherwise noted)

Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
Off Characteristics						
BV_{DSS}	Drain-Source Breakdown Voltage	V_{GS} = 0 V, I_D = 250 μA	650	--	--	V
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS} = 650 V, V_{GS} = 0 V	--	--	1	μA
		V_{DS} = 650 V, T_C = 125℃	--	--	100	
I_{GSSF}	Gate-Body Leakage Current, Forward	V_{GS} = 30 V, V_{DS} = 0 V	--	--	100	nA
I_{GSSR}	Gate-Body Leakage Current, Reverse	V_{GS} = -30 V, V_{DS} = 0 V	--	--	-100	nA
On Characteristics						
$V_{GS(th)}$	Gate Threshold Voltage	V_{DS} = V_{GS}, I_D = 250 μA	2	--	4	V
$R_{DS(on)}$	Static Drain-Source on-Resistance	V_{GS} = 10 V, I_D = 5.5A	--	0.34	0.38	Ω
g_{FS}	Forward Transconductance	V_{DS} = 10V, I_D = 5.5A	--	8.7	--	S
Dynamic Characteristics						
C_{iss}	Input Capacitance	V_{DS} =100V , V_{GS} = 0 V, f = 1.0 MHz	--	750	--	pF
C_{oss}	Output Capacitance		--	42	--	pF
C_{rss}	Reverse Transfer Capacitance		--	3.1	--	pF
Switching Characteristics						
$t_{d(on)}$	Turn-On Delay Time	V_{DS} = 325 V, I_D = 10.6A R_G = 25 Ω , V_{GS} =10V	--	20	--	ns
t_r	Turn-On Rise Time		--	40	--	ns
$t_{d(off)}$	Turn-Off Delay Time		--	110	--	ns
t_f	Turn-Off Fall Time		--	36	--	ns
Q_g	Total Gate Charge	V_{DS} = 520 V, I_D = 10.6A V_{GS} = 10V	--	21	--	nC
Q_{gs}	Gate-Source Charge		--	5	--	nC
Q_{gd}	Gate-Drain Charge		--	7.5	--	nC
Drain-Source Diode Characteristics and Maximum Ratings						
I_S	Maximum Continuous Drain-Source Diode Forward Current		--	--	11	A
I_{SM}	Maximum Pulsed Drain-Source Diode Forward Current		--	--	44	A
V_{SD}	Drain-Source Diode Forward Voltage	V_{GS} = 0 V, I_S = 9A	--	--	1.4	V
t_{rr}	Reverse Recovery Time	V_{GS} = 0 V, I_F = 7A dI_F / dt = 100 A/ μs	--	324	--	ns
Q_{rr}	Reverse Recovery Charge		--	3.8	--	μC

Notes:

1.The EAS data shows Max. rating .The test condition is V_{DS}=80V , V_{GS}=10V , L=5mH , I_{AS}=5.5A.

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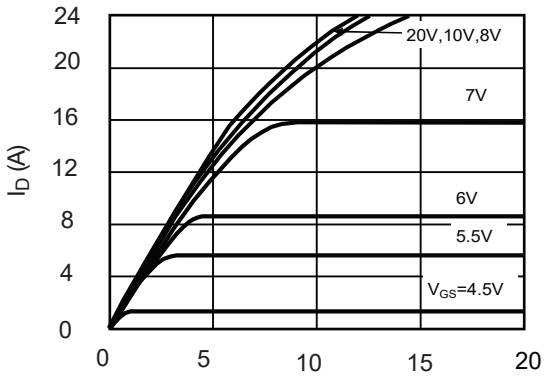
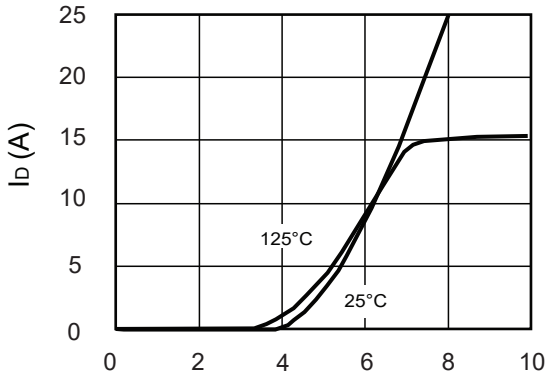
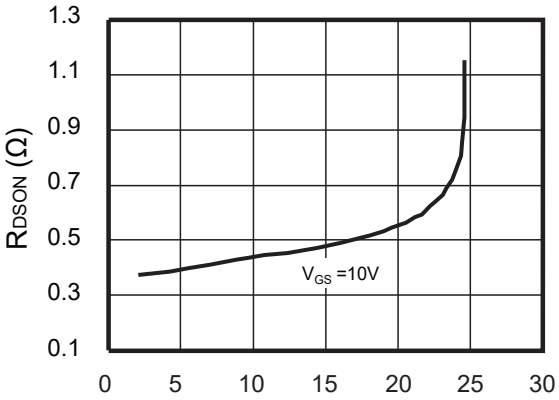
Typical Characteristics



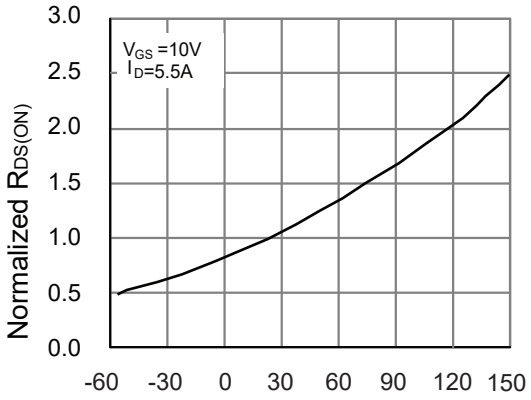
Output Characteristics



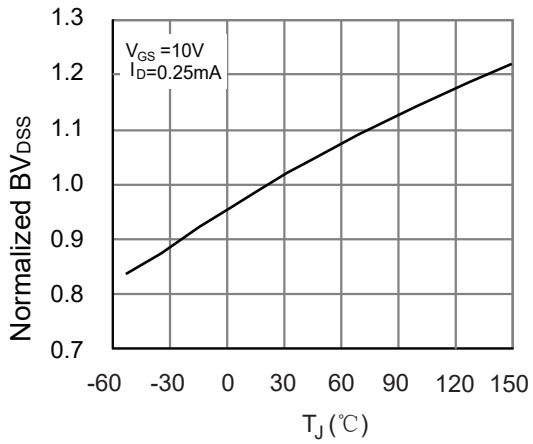
transfer characteristics



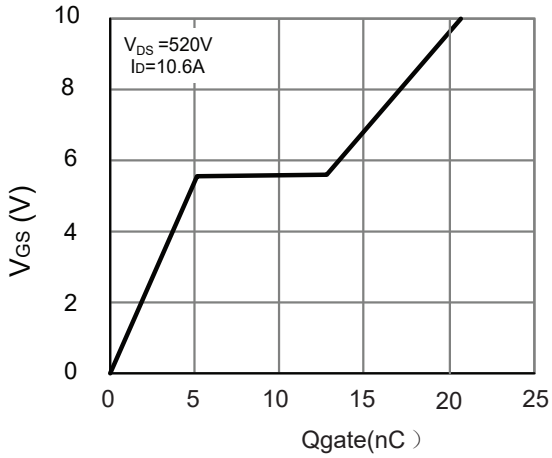
drain-source on-resistance



On-Resistance vs. Junction Temperature

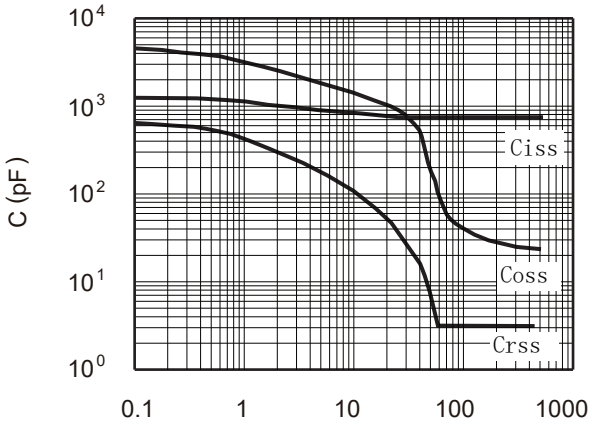


Breakdown Voltage Variation vs. Temperature

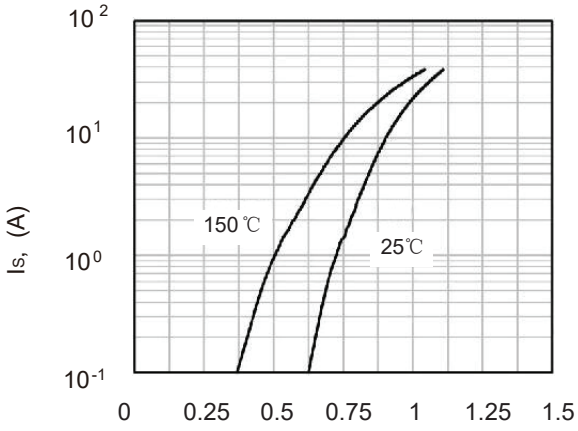


Gate charge vs gate-source voltage

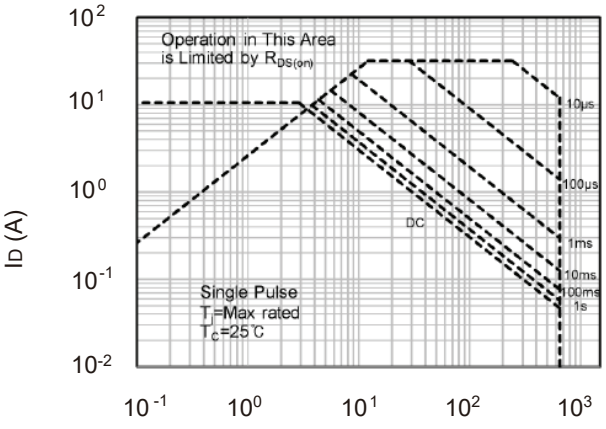
Typical Characteristics



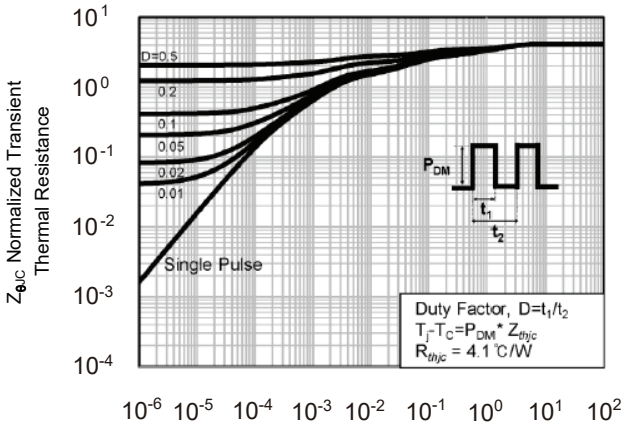
Capacitance Characteristics



Body-Diode Characteristics



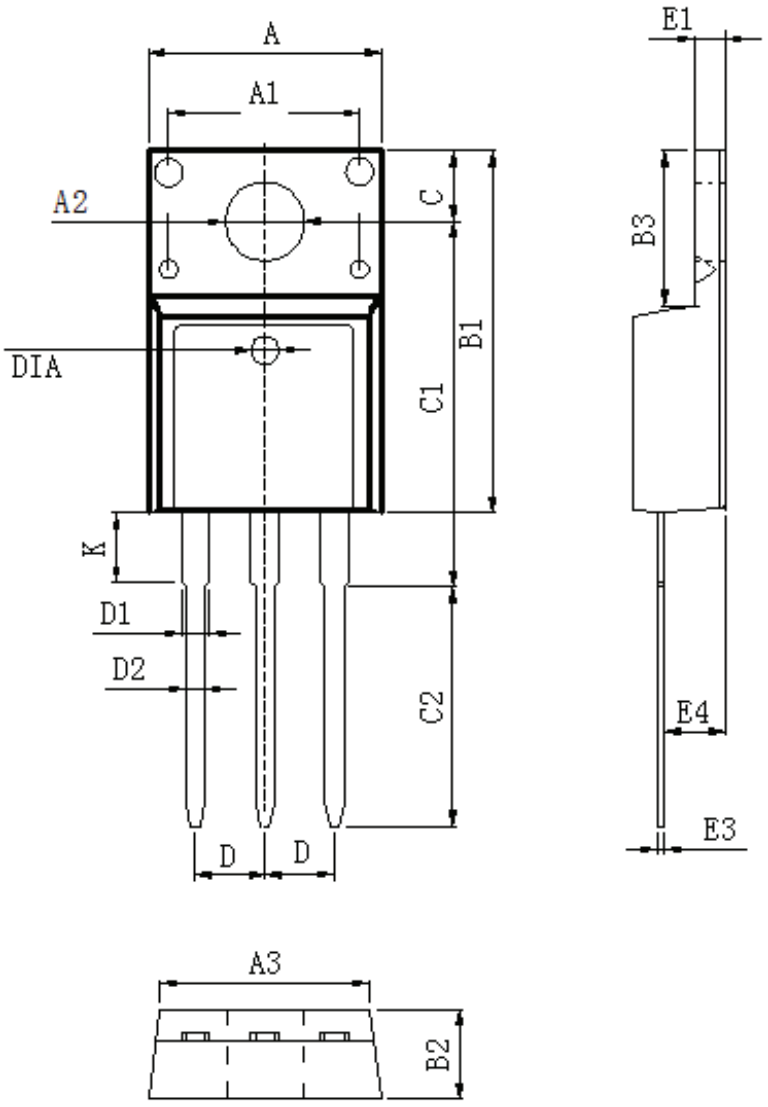
Safe operating area



Normalized Maximum Transient Thermal Impedance

Package Dimension

TO-220F Unit :mm



DIM	MILLIMETERS
A	10.16±0.3
A1	7.00±0.1
A2	3.3±0.2
A3	9.5±0.2
B1	15.87±0.3
B2	4.7±0.2
B3	6.68±0.4
C	3.3±0.2
C1	12.57±0.3
C2	10.02±0.5
D	2.54±0.05
D1	1.28±0.2
D2	0.8±0.1
K	3.1±0.3
E1	2.54±0.1
E3	0.5±0.1
E4	2.76±0.2
DIA	⊙1.5(deep 0.2)